BAV70 series

High-speed switching diodes

Rev. 07 — 27 November 2007

Product data sheet

Product profile

General description

High-speed switching diodes, encapsulated in small Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview**

Type number	Package	Package			Configuration	
	NXP	JEITA	JEDEC	configuration	COM.TW	
BAV70	SOT23	COM	TO-236AB	small	dual common cathode	
BAV70M	SOT883	SC-101	TW	leadless ultra small	dual common cathode	
BAV70S	SOT363	SC-88	LTW	very small	quadruple common cathode/common cathode	
BAV70T	SOT416	SC-75	TW	ultra small	dual common cathode	
BAV70W	SOT323	SC-70	DVI.	very small	dual common cathode	
		- ANN 1-1-			- 11W 1 b	

WWW.100Y.COM WWW.100 1.2 **Features**

- High switching speed: t_{rr} ≤ 4 ns
- Low leakage current
- Small SMD plastic packages
- Low capacitance: C_d ≤ 1.5 pF
- Reverse voltage: V_R ≤ 100 V

1.3 **Applications**

- High-speed switching
- General-purpose switching

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min T	ур Мах	Unit
Per diode	I.CO. TIN				
I_R	reverse current	$V_{R} = 80 \text{ V}$	CONTIN -	0.5	μΑ
V_{R}	reverse voltage	WWW.	Y.COM.	100	V
t _{rr}	reverse recovery time	TWW.100	[1]	4	ns

^[1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

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2. Pinning information

Table 3. **Pinning** Pin Description Simplified outline **Symbol** BAV70; BAV70T; BAV70W 1 anode (diode 1) 3 2 anode (diode 2) common cathode 3 2 006aaa144 BAV70M anode (diode 1) anode (diode 2) common cathode Transparent top view BAV70S anode (diode 1) anode (diode 2) common cathode (diode 3 and diode 4) anode (diode 3) anode (diode 4) 2 3 006aab104 common cathode (diode 1 and diode 2)

3. Ordering information

Table 4. Ordering information

Type number	Package			
	Name	Description	Version	
BAV70	W.T.W	plastic surface-mounted package; 3 leads	SOT23	
BAV70M	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883	
BAV70S	SC-88	plastic surface-mounted package; 6 leads	SOT363	
BAV70T	SC-75	plastic surface-mounted package; 3 leads	SOT416	
BAV70W	SC-70	plastic surface-mounted package; 3 leads	SOT323	
			- 4 J J J J J J	

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4. Marking

Table 5. Marking codes

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Marking code ^[1]
A4*
S4 1000
A4*
A4
A4*

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5. Limiting values WWW.100

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
V_{RRM}	repetitive peak reverse voltage		WWW.10	100	V
V_{R}	reverse voltage	OM.	WWW.	100	OV.
IF	forward current	COM:	WWW.	100	COM
	BAV70	T _{amb} ≤ 25 °C	- 311	215	mA
	BAV70M	T _s = 90 °C	M	150	mA
	BAV70S	T _s = 60 °C	-11/11	250	mA
	BAV70T	T _s = 90 °C	- 717	150	mA
	BAV70W	T _{amb} ≤ 25 °C	W - W	175	mA
I _{FRM}	repetitive peak forward current				
	BAV70	100 Y.CO	TW -	450	mA
	BAV70M	W. TOOX.COM	TW -	500	mA
	BAV70S		TW-	450	mA
	BAV70T	N. Jon S. C.C.	M	500	mA
	BAV70W	11W.1007	OWIT	500	mA
I _{FSM}	non-repetitive peak forward	square wave	<u>[1]</u>		100
	current	$t_p = 1 \mu s$	M.T.W	4	Α
MW.L	OV.CON.	$t_p = 1 \text{ ms}$	COLTY	1	Α
寺力 材料	- 886-3-5753170	$t_p = 1 \text{ s}$	Y.CON.	0.5	Α
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BAV70 SER 7

^{[1] * = -:} made in Hong Kong

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

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Table 6. Limiting values ... continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation		[2]		
	BAV70	T _{amb} ≤ 25 °C	TOM.TW	250	mW
	BAV70M	T _{amb} ≤ 25 °C	[3]	250	mW
WWW.I	BAV70S	T _s = 60 °C	Y.COPT. TV	350	mW
	BAV70T	T _s = 90 °C	N.COI	170	mW
	BAV70W	T _{amb} ≤ 25 °C	CGM	200	mW
Per device	W.100Y. COM.TW	WW.1	mr. COM.	1 1	
I _F	forward current	1001. COM	III		
	BAV70	T _{amb} ≤ 25 °C	1007:	125	mA
	BAV70M	T _s = 90 °C	1007-CO	75	mA
	BAV70S	T _s = 60 °C	M. T. CC	100	mA
	BAV70T	T _s = 90 °C	M.To.	75	mA
	BAV70W	T _{amb} ≤ 25 °C	WW.100	100	mA
Tj	junction temperature	W.TW W	7. F00 7.	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature	TW	-65	+150	°C
1		U/Az-	-4111		-1

^[1] $T_i = 25$ °C prior to surge.

Thermal characteristics 6.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]			
	BAV70			-	500	K/W
	BAV70M		[2] _	- 1/1	500	K/W
	BAV70W	N 11 100 Y.CO	MITW.	- 1	625	K/W
$R_{th(j-t)}$	thermal resistance from junction to tie-point	WW.100Y.CC	OM.TW		NN	
	BAV70	W 1001.	OM.TY	-	360	K/W
R _{th(j-sp)}	BAV70W	WW 1007.	TOM.TW	-	300	K/W
	thermal resistance from junction to solder point	WWW.100Y	V.COM.TV			IMM
	BAV70S	WW.100	COM.	-XXI	255	K/W
	BAV70T	W W 10	07.	Lin	350	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[3] Reflow soldering is the only recommended soldering method.

Reflow soldering is the only recommended soldering method.

7. Characteristics

Table 8 **Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max
Per diode					
V _F	forward voltage		<u>[1]</u>		
		$I_F = 1 \text{ mA}$	COA	TV	715
		I _F = 10 mA	CG_{M_I}	TIN	855
		$I_F = 50 \text{ mA}$	J CON	1.1	1
		I _F = 150 mA	-00	WILL	1.25
I _R	reverse current	V _R = 25 V	07:	N.T.TV	30
		V _R = 80 V	00 7.C	-i11	0.5
		$V_R = 25 \text{ V}; T_j = 150 ^{\circ}\text{C}$	100-X.C	O.	30
		$V_R = 80 \text{ V}; T_j = 150 ^{\circ}\text{C}$	To.	$C_{\mathbf{O}_{Mr}}$	100
C _d	diode capacitance	V _R = 0 V; f = 1 MHz	1.100	CON	1.5
t _{rr}	reverse recovery time		[2]	- CO	4
V_{FR}	forward recovery voltage	WIN WIN	[3]	J.	1.75

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^[2] When switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100$ Ω; measured at $I_R = 1$ mA.

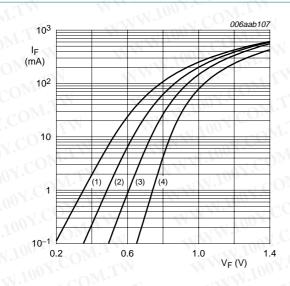
[3] When switched from $I_F = 10$ mA: $t_r = 20$ ps WWW.100Y.COM.TW ... Switched from $I_F = 10$ mA to $I_R = 10$ rg. [3] When switched from $I_F = 10$ mA; $t_r = 20$ ns. WWW.100Y.COM.TW

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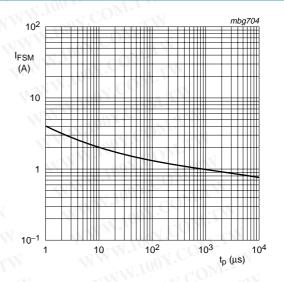
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- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \,^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

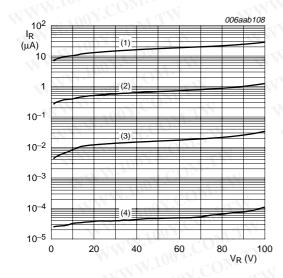
Fig 1. Forward current as a function of forward voltage; typical values



Based on square wave currents.

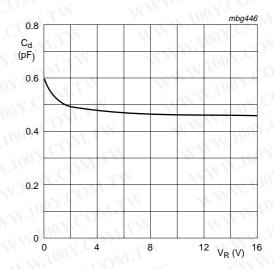
T_i = 25 °C; prior to surge





- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 85 \,^{\circ}C$
- (3) $T_{amb} = 25 \,^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

Fig 3. Reverse current as a function of reverse voltage; typical values

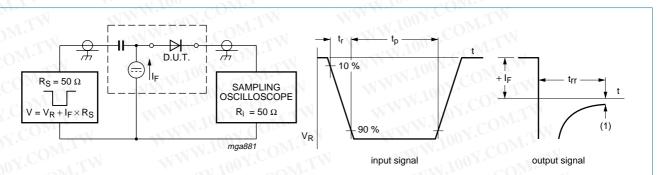


 $f = 1 \text{ MHz}; T_{amb} = 25 \,^{\circ}\text{C}$

Fig 4. Diode capacitance as a function of reverse voltage; typical values

6 of 15

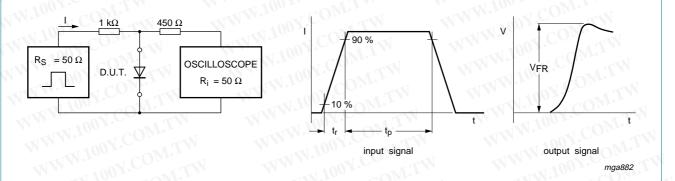
8. Test information



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(1) $I_R = 1 \text{ mA}$ Input signal: reverse pulse rise time $t_r = 0.6$ ns; reverse voltage pulse duration $t_p = 100$ ns; duty cycle $\delta = 0.05$ Oscilloscope: rise time $t_r = 0.35$ ns

Fig 5. Reverse recovery time test circuit and waveforms



Input signal: forward pulse rise time t_r = 20 ns; forward current pulse duration $t_p \ge 100$ ns; duty cycle $\delta \le 0.005$

Forward recovery voltage test circuit and waveforms

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9. Package outline

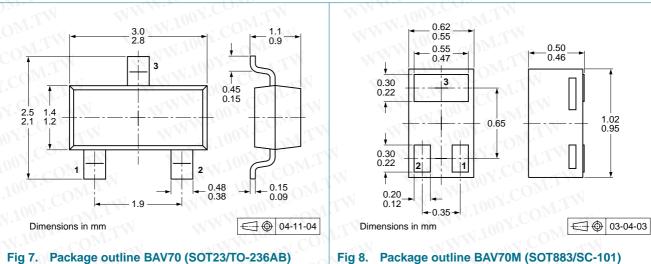


Fig 7. Package outline BAV70 (SOT23/TO-236AB)

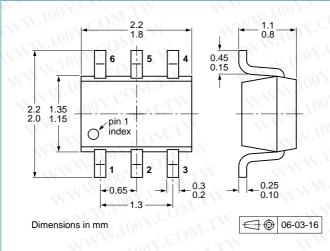


Fig 9. Package outline BAV70S (SOT363/SC-88)

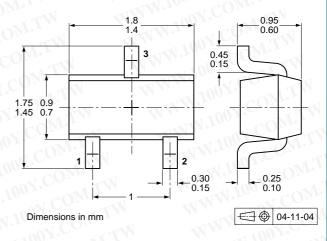


Fig 10. Package outline BAV70T (SOT416/SC-75)

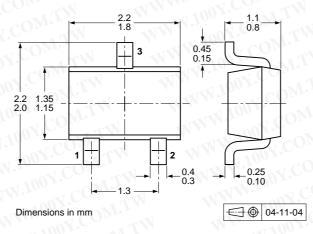


Fig 11. Package outline BAV70W (SOT323/SC-70)

10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

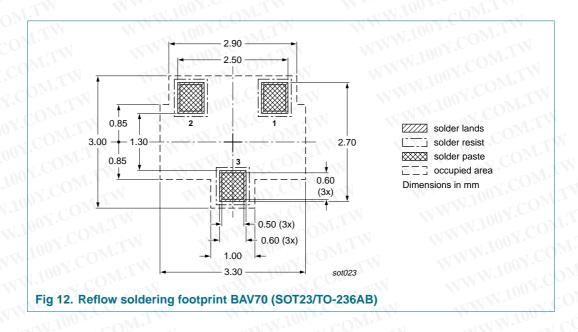
Type number	Package	Description	LAL	Packing	quantity
				3000	10000
BAV70	SOT23	4 mm pitch, 8 mm tape and reel		-215	-235
BAV70M	SOT883	2 mm pitch, 8 mm tape and reel	T	Ñ	-315
BAV70S SOT36	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-165
BAV70T	SOT416	4 mm pitch, 8 mm tape and reel		-115	-135
BAV70W	SOT323	4 mm pitch, 8 mm tape and reel		-115	-135

[1] For further information and the availability of packing methods, see Section 14.

[2] T1: normal taping

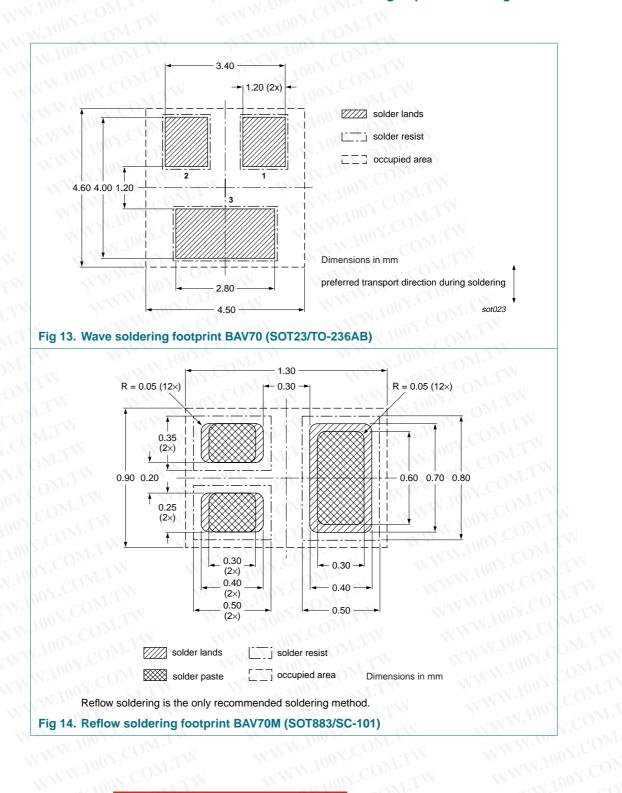
[3] T2: reverse taping

11. Soldering



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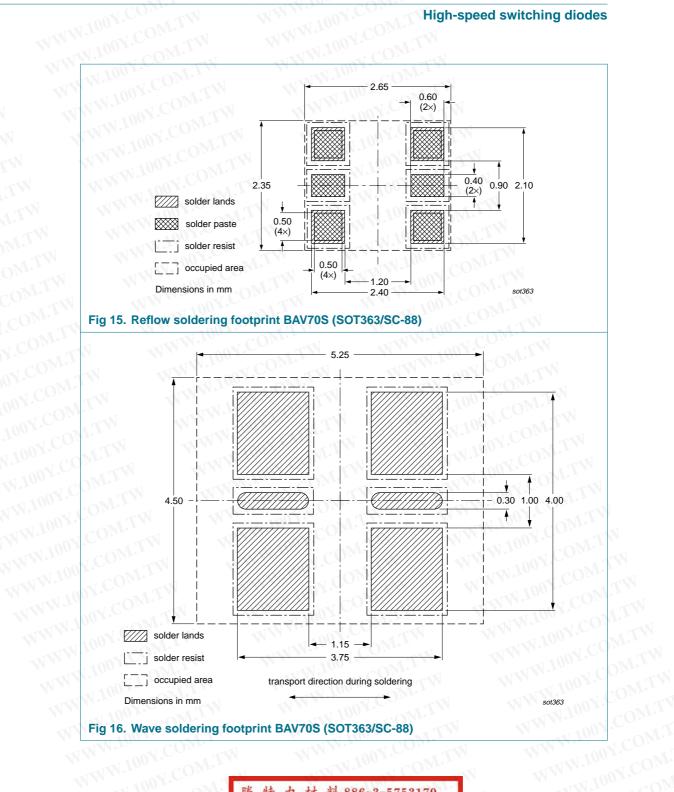


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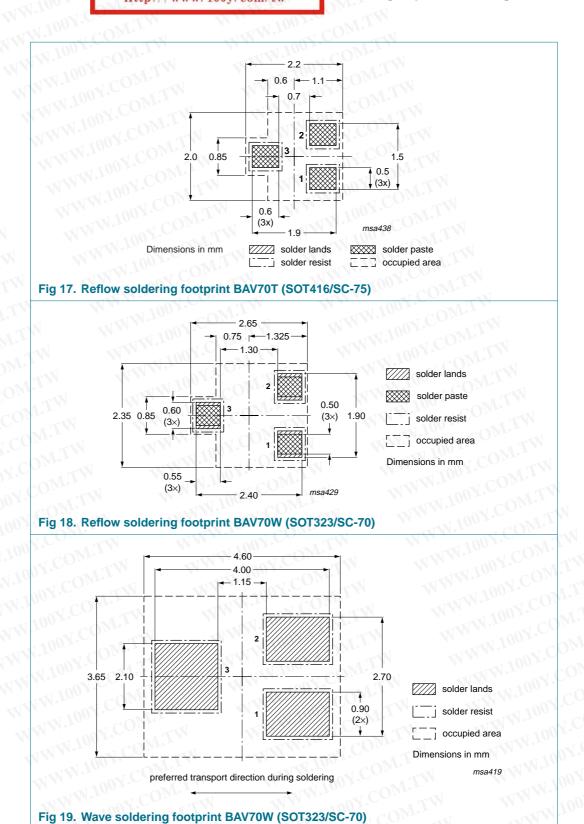
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100Y.COM.TW 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAV70_SER_7	20071127	Product data sheet	WWW.100X.COM	BAV70_6 BAV70S_2 BAV70T_3 BAV70W_6
Modifications:	guidelines Legal texts Type numb Section 1.1 Table 1 "Pr Table 2 "Qu Table 6 "Lin value from Table 6 "Lin from 75 V t Table 8 "Ch IR condition Table 8 "Ch from 2.5 µA Table 8 "Ch IR maximur Table 8 "Ch IR condition Table 8 "Ch IR condition Section 8 "	to 100 V paracteristics": for BAV70, E to V_R from 75 V to 80 V for paracteristics": for BAV70, E A to 0.5 μ A for $T_j = 25$ °C paracteristics": for BAV70T	new company name wherended BAV70S and BAV70W chapped and BAV70W chapped of I_R maximum where I_R and I_R and I_R maximum where I_R condition I_R and I_R	ere appropriate. Handle appropriate appropriate and the appropriate and the appropriate and the appropriate appropriate and the appropriate appropriate and the appropriate appropriate and the appropriate appropriate appropriate and the appropriate appropriate appropriate appropriate and the appropriate appropriate appropriate appropriate appropriate and the appropriate appropria
	* UII]	"Soldering": added "Legal information": update	ed	
BAV70_6	20020403	Product specification	In COM:	BAV70_5
BAV70S_2	19971021	Product specification	100 1. COM'I A.	BAV70S_1
BAV70T_3	20040204	Product specification	100 Y. COM.TW	BAV70T_2
BAV70W_6	20020405	Product specification	TINOY	BAV70W_5

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- 1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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